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High harmonic generation from a multi-jet gas puff target for FEL seeding

T. Fok [1]*, Ł. Węgrzyński[1], M. Kozlova[2], J. Nejdl[2], P.W. Wachulak[1], R. Jarocki[1], A. Bartnik[1] and H. Fiedorowicz[1]

[1]*Institute of Optoelectronics, Military University of Technology, Kaliskiego 2, 00-908 Warsaw,*
[2]*Institute of Physics, The Academy of Sciences of the Czech Republic, Na Slovance 2, 182 21 Prague*

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*e-mail: tfok@wat.edu.pl

As a result of interaction of ultra-short, high power laser pulses with gases high-order harmonics generation (HHG) occurs. It is the most promising methods to obtain coherent radiation in the soft X-ray (SXR) and extreme ultraviolet (EUV) regions [1, 2]. This radiation is highly attractive for applications in various areas, including seeding of a free electron laser (FEL) [3].

Seeding of FEL with an external source will improve the temporal coherence, ensure high shot-to-shot stability and high peak power, and will decrease the saturation length. This method was presented e.g. on Spring-8 Compact SASE Source (Japan) [4] and FLASH FEL (Germany) [5].

In this paper we present the recent results of HHG experiments with the use of a multi-jet gas puff target, developed at the Institute of Optoelectronics, MUT [6]. The results should be useful for the development of an efficient, quasimonochromatic source of coherent EUV radiation [7], with potential application to FEL seeding.

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Extreme ultraviolet surface modification of fluoropolymers for biocompatibility control

I. U. Ahad[1,2], M. Ayele[1]*, B. Butruk[3], B. Korczyc[1], B. Budner[1], D. Adjei[1], A. Bartnik[1] , H. Fiedorowicz[1], T. Ciach[3] and D. Brabazon[2]

[1]*Institute of Optoelectronics, Military University of Technology, 00-908 Warsaw, Poland*
[2]*Advanced Processing Technology Research Centre Dublin City University, Dublin 9, Ireland*
[3]*Department of Biotechnology and Bioprocess Engineering, Warsaw University of Technology, 00-645 Warsaw, Poland*

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*e-mail: mgayele@wat.edu.pl

Recent advancements in organic materials as “Green Alternatives” in various applications dramatically increased the requirement of efficient surface modification technique which would be able to tune the surface properties without altering mechanical properties of bulk materials[1][2]. The thickness of such materials (e.g biosensors, bio-mimetic artificial implants, artificial muscles, organic electrodes for biomedical engineering applications, and many more) will be limited to few millimeters or up to few hundred microns in particular applications. The conventional ultraviolet (UV) and plasma based techniques produce undesirable effects such as alteration of bulk material properties. This problem limit their applicability in biomedical engineering applications. Extreme ultraviolet (EUV) photons with energies from 30 eV up to 250 eV (corresponding to wavelengths in vacuum from 40 nm to 5 nm respectively) have limited penetration depths (up to 100 nm) in to the polymer surface[3]. Therefore the modification of physical and chemical properties will be limited to upper layer surface and the bulk properties will remain intact. EUV photons can be produced by synchrotron radiation (SR) sources or laser-plasma sources. The limited number and accessibility to large scale SR facilities encouraged the development of compact laboratory EUV sources. Such sources are currently being used by a few groups to investigate new applications of EUV technology in various fields.

This study demonstrates the use of EUV surface modification technique in biomedical engineering applications. Micro and nano-patterned surfaces, functionalized with special reactive groups are often desirable for improved biocompatibility of various polymers in vascular prosthesis and tissue engineering applications. A number of polymers such as PC, PET, PTFE and PVF have been irradiated with a laser-plasma EUV source based on a double-stream gas-puff target, irradiated with the 3 ns/0.8J Nd:YAG laser pulse at 10Hz [4]. The EUV irradiated samples were characterized through SEM, AFM, XPS and water contact angle measurements. The irradiation of EUV photons on

polymer surfaces resulted in the formation of nano- and micro-patterning. It has been demonstrated that tuning of physical and chemical properties is possible by EUV surface modification. Increased surface roughness up to many folds, controlled wettability (increased hydrophilicity or hydrophobicity as per requirements) and improved biocompatibility levels (improved cell attachment and cell adhesion) have been observed. Fig. 1 demonstrates improved cell attachment of L929 fibroblasts on EUV irradiated PTFE surface (b) as compared to pristine control sample (a).

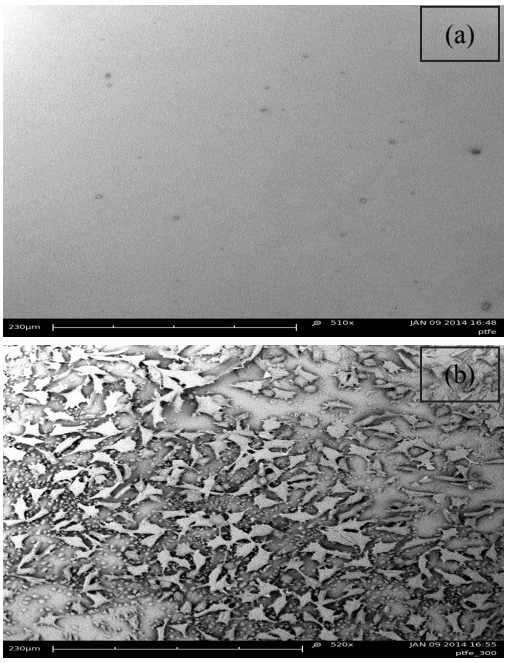

Fig. 1 SEM images of washed PTFE surfaces after incubated with L929 fibroblasts for 24 hours (a) pure sample, (b) irradiated with 300 EUV shots.

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X-Ray Absorption and Resonant Photoemission studies of Fe doped $SrTiO_3$ films for different parameters of PLD deposition

J. Kubacki[1]*, D. Kajewski[1], A. Koehl[2] and J. Szade[1]

[1]*Silesian Centre of Research and Education, Institute of Physics, University of Silesia, 75 Pulku Piechoty 1, 141-500 Chorzow, Poland*
[2]*Peter Gruenberg Institute and JARA-FIT, FZ Juelich, D-52425 Juelich, Germany*

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*e-mail: jerzy.kubacki@us.edu.pl

The $SrTiO_3$ is an insulator with the energy gap of 3.2 eV, for which the nature of the resistive switching process was described in the filamentary model [1]. The STO thin film has promising properties of the resistive switching for future RRAM application [2]. Doping by acceptor and donor allow tuning of the electrical properties for this material. The doping is crucial for the electronic structure, especially in the energy gap. Last time the most of studies of Nb, Mn and Fe doping STO films were performed from the resistive switching process point of view [3-5]. In our work we focused on Fe doping and its contribution to the valence band. Three samples with different amount of defects were prepared by changing the PLD parameters, i.e. oxygen pressure and energy of laser. In order to describe the contribution of the Fe and main components to the electronic structure, the X-Ray Absorption Spectroscopy and Resonant Photoemission Studies were performed.

The epitaxial Fe doped STO films with thickness of about 20 nm were obtained by PLD (Pulsed Laser Deposition) method on the Nb doped $SrTiO_3$ single crystal substrate. Three samples 2% Fe doped $SrTiO_3$ were studied for three various parameters of PLD deposition. The samples were annealed in UHV conditions prior to study at 150ºC, 300 ºC and 630 ºC.

The Ti $L_{2,3}$, Fe $L_{2,3}$ and O K XAS spectra were obtained with used to of the two methods – total electron yield (TEY) measured by the drain current and Auger electron yield (AEY). The methods have different surface sensitivity.

The XAS spectra showed that Fe presents in the sample in two oxidation states 2+ and 3+. The relative content of these states is dependent on the deposition parameters.

The different parameters of the film deposition led to changes in the structure of the valence band, especially in partial density of states (PDOS) for broad Fe^{2+} structure and intensity of the top valence band Fe^{3+} components.